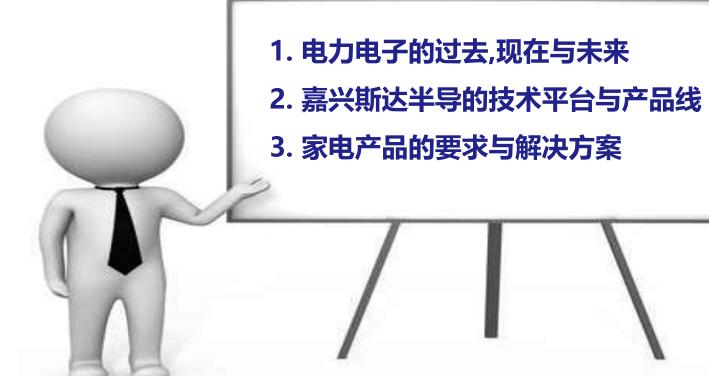
## 嘉兴斯达半导体高性能功率器件携手家电产业 共创美好未来





Norman Day
Technology Division
Vice President







## Philosophy V.S. Technology

物竞天择,适者生存,不适者淘汰 达尔文进化论

我们无法驾驭变革,我们只能走在变革之前

管理大师P. F. Drucker

人法地,地法天,天法道,道法自然

道德经.二十五章.老子 starpower

## Part One

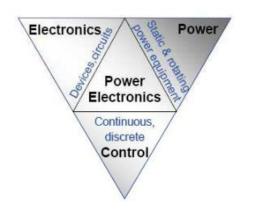
# 电力电子的过去, 现在与未来

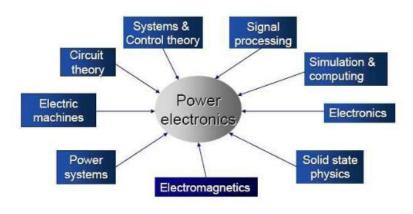


### What is Power Electronics?

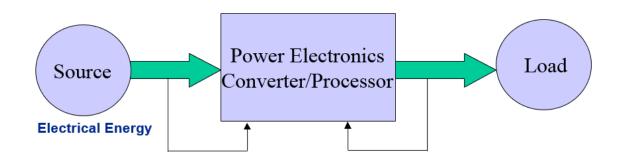
电力电子学(Power Electronics)这一名称是在上世纪60年代出现的。1974年,美国的W.Newell用一个倒三角形对电力电子学进行了描述,认为它是由<u>电力学</u>、<u>电子学和控制理论</u>三个学科交叉而形成的。

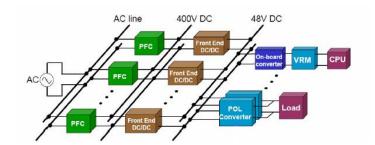
#### Something is missing?

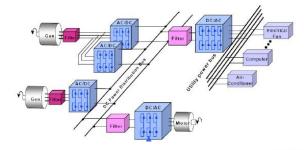




### Power Electronics Realization

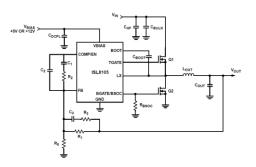






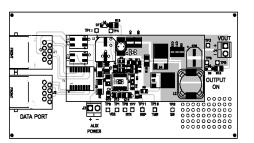
### Technology Trend For DC to DC Converter

- Effects of Switching Frequency
  - Inductance  $\propto 1/f \rightarrow f \uparrow \rightarrow \text{ inductor size } \downarrow$
  - $f \uparrow \rightarrow$  converting efficiency  $\downarrow$
- Technology Trend
  - FoM of Power devices will be never come to the end
  - Small and low profile inductor is necessary

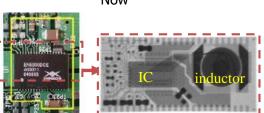


### $\rightarrow$ Compact layout $\rightarrow$ SiP $\rightarrow$ SoC More than Moore

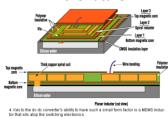
Past



Now

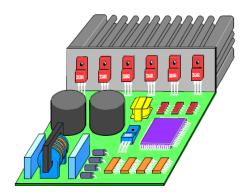


In the future



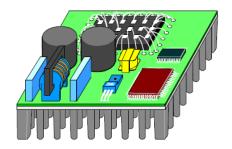


## Technology Trend For Motor Drive



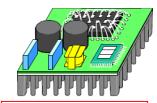
Discrete solution with mature topology and devices technology.

Modularized, driving algorithm and overall system cost effective solution are the main driving force



Power semiconductors integrated more function, packaging platform is not limited, system size further reduction.

Power density, and higher reliability are the main driving force

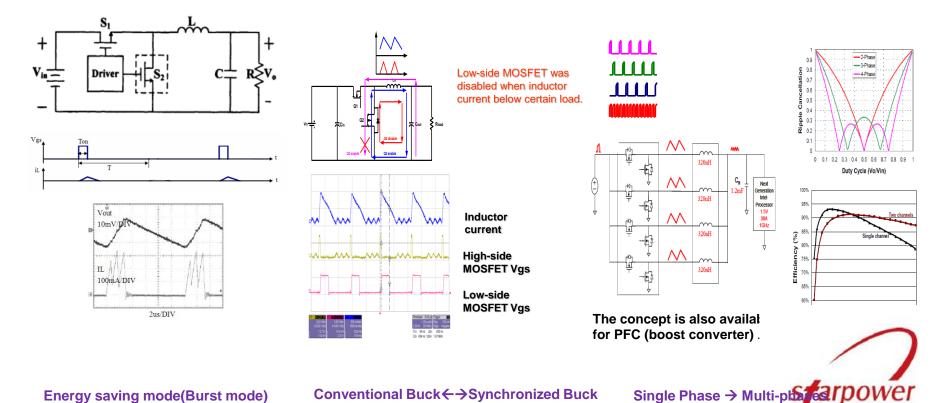


Integrated power devices with sensing circuit in wafer level except for energy storage components.

Re-allocated circuitry design concept, packaging and revolution design are the main driving force



### Intelligent Control Algorithm for Efficiency Improvement



Starpower Confidential

## Technology Trend for Power Electronics

31

Integration, Intelligent, Innovation





# Part One

嘉兴斯达半导体 的技术平台与产 品线



## Company Profile

■ Established: on April 27, 2005

■ Campus: 70,700 m2

■ Total employees: 640

■ Revenue in 2018: \$ 120 million USD





- Mass Production\_ over 10 years
- Monthly output\_ over 600 thousands of IGBT modules



- Advanced production equipment
- Main equipments \_ purchased from Germany, American and Japan
- Clean Room\_ 4500 square meters



- 100% on-line monitoring\_ on each technological step
- ERP system traceability for each module in production and after shipment

#### Shanghai Dosemi



- · Located in Shanghai New Energy Veichle Science Park
- · Focus on IGBT modules for EV application
- · Start production in Q4, 2017

#### **Zhejiang Dosemi**



- Products including rectifier modules, FRD modules, discrete products etc...
- In production since 2013.

#### StarPower Europe R&D Center (Nurnberg)



- 1. 10 senior power semiconductor chips and module R&D engineers WCF
- 2. Advanced process and analysis equipment in the lab;

#### IGBT Module Market Share in Global-Year 2015

Table 4.15 - World Total IGBT-based Module Supplier Market Share Estimates (US \$ Revenues)

2015 R	ank Manufacturer	2014r share	2015 share	Change
1	Infineon Technologies*	21.9%	24.5%	2.6%
2	Mitsubishi (inc. Powerex)	25.8%	24.4%	-1.4%
3	Fuji Electric	12.3%	12.2%	0.0%
4	Semikron	9.2%	9.7%	0.5%
5	Hitachi	2.9%	3.2%	0.4%
6	ON Semiconductor	3.1%	3.1%	0.0%
7	Vincotech	2.4%	2.9%	0.5%
8	ABB Semiconductors	2.2%	2.6%	0.4%
9	Fairchild Semiconductor	2.4%	2.5%	0.1%
10	Danfoss	1.5%	1.7%	0.2%
11	Starpower Semiconductor	1.6%	1.6%	0.0%
12	Toshiba	2.4%	1.4%	-1.0%
13	Bosch	0.5%	1.2%	0.7%
14	IXYS	1.0%	1.2%	0.2%
15	CRRC Times Electric (inc. Dynex)	0.2%	0.6%	0.4%
	International Rectifier*	2.2%	N/A	N/A
	Others	8.3%	7.1%	-1.2%
	Total Market Size =	\$3,558.9 m	\$3,091.9 m	-13.1%

#### Notes

r= revised since 2015 edition

Source: IHS

© 2016 IHS



<sup>\*</sup> Infineon Technologies acquired International Rectifier in Jan 2015. Both companies are reported seperately in 2014 and combined as Infineon in 2015.

#### IGBT Module Market Share in China- Year 2015

Power Semiconductor Intelligence Service - 2016

2015 Rank	Manufacturer	2014r share	2015 share	Change
1	Infineon Technologies*	29.2%	23.4%	-5.8%
2	Mitsubishi (inc. Powerex)	19.9%	19.0%	-0.9%
3	Fuji Electric	13.2%	15.5%	2.3%
4	Semikron	9.3%	11.8%	2.5%
5	Starpower Semiconductor	4.5%	4.5%	0.1%
ŝ.	ON Semiconductor	4 7%	4 4%	-0.3%
7	ABB Semiconductors	2.6%	3.9%	1.4%
3	Vincotech	2.5%	3.9%	1.4%
9	IXYS	1.5%	1.8%	0.3%
10	CRRC Times Electric (inc. Dynex)***	0.4%	1.6%	1.2%
11	Fairchild Semiconductor	1.2%	1.3%	0.1%
12	Hitachi	0.2%	1.1%	0.9%
13	Danfoss	0.7%	1.0%	0.3%
	International Rectifier*	2.2%	N/A	N/A
	LS Power Semitech**	1.1%	N/A	N/A
	Others	7.0%	6.8%	-0.2%

#### Notes

r= revised since 2015 edition

Source: IHS

<sup>\*</sup> Infineon Technologies acquired International Rectifier in Jan 2015. Both companies are reported seperately in 2014 and combined as Infineon in 2015.

<sup>\*\*</sup> Infineon also took a controlling interest in former JV company LS Power Semitech part way through 2014.

<sup>\*\*\*</sup> Zhuzhou CSR Times Electric Co., Ltd (the owners of Dynex Semiconductor Ltd.) and China CNR Corporation merged in June 2015 to form Zhuzhou CRRC Times Electric Co., Ltd.

#### 2016 Global IGBT Module Market Share

Power Semiconductor Intelligence Service

Annual Power Semiconductor Market Share Report / August 2017

#### 4.1 The world market for power modules

The power module market was worth an estimated \$4.12 billion in 2016, an increase of 3.5% from 2015. Standard IGBT modules accounted for the most revenues, an estimated 45.7% of the 2016 total.

Revenues increased for four of the six power module product types in 2016; revenues for two declined.

The products with growing markets were MOSFET modules (by 31.5%), MOSFET-IPMs (by 19.3%), PIM/CIBs (by 3.3%), and Standard IBT modules (by 2.2%, slightly less than overall average).

The products with declining markets were thyristor-diode modules (-2.7%) and IGBT-IPMs (-0.5%).

Infineon Technologies had overtaken Mitsubishi Electric to become the leading power module manufacturer in 2015. In 2016, it extended its lead, increasing its share by 0.9 percentage points.

Mitsubishi lost market share due, in part, to the temporary closure of its Kumamoto power module production plant following an earthquake in April 2016.

Once again, the top 4 suppliers took almost 60% of the total power module market. However, having acquired Fairchild, ON Semiconductor has established itself firmly in 5th place in the power module market ranks.

		2015r	2016	15-10
1	Infineon Technologies	20.5%	21.4%	0.9%
2	Mtsubishi (inc. Powerex)	19.4%	17.8%	-1.69
3	Fuji Electric	9.5%	9.6%	0.19
4	Semikron	10.0%	9.3%	-0.79
5	ON Semiconductor	2.4%	6.0%	3.69
6	Vincotech	2.5%	3.4%	0.99
7	IXYS	2.7%	2.7%	0.09
8	Danfoss	2.4%	2.7%	0.39
9	Starpower Semiconductor	2.1%	2.5%	0.39
10	Bosch	1.5%	2.0%	0.59
	Others	27.1%	22.8%	-4.39
	Total market size =	\$3.98 billion	\$4.12 billion	3.5%



#### Partail Customers in China



















































#### Partail Customers in Oversea



































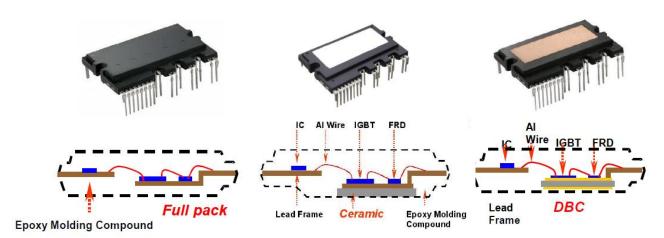




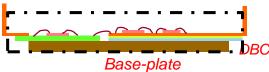
### Process Flow of Power Semiconductor Packaging

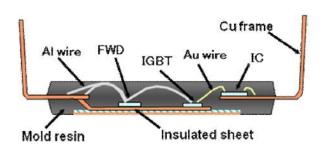


## Power Packaging Platform(Transfer Molding)

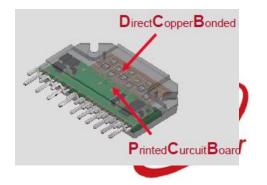












#### **Product Portfolio**

#### 小功率IGBT模块系列



中等功率IGBT模块系列



碳化硅模块及IPM模块







大功率IGBT模块系列









电动汽车用IGBT 模块



## Part Two

# 家电系统的要求 及解决方案



## Why IPM?

Co-pack

**HVICs LVICs** 

**IGBTs/Diodes** 













More component counts mean higher failure rate intrinsic and longer manufacturing time might involve more potential failure factors

**Integrated** components by single package is able to save assembly time and enhance the reliability

Additional parasitic effect by using external trace connecting on PCB, caused more time delay

**Built-in HVIC and** LVIC/Buffer IC with protection function



#### **Design Viewpoint**

Fine tune switching performance and using external components are needed

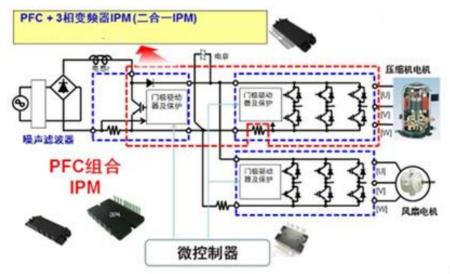
Standardized driving design for built-in power devices

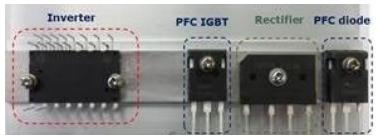
- **Reduced overall system cost**
- **Shorten development time**
- Parasitic effect reduction
- Easy assembly & system size reduction
- **Material control effort reduction**
- Higher power density & reliability

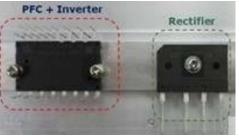


**Assembly Impact** 

### **Not Just Power Integration**







## Available Solution for Home Appliance



封装类别	电路拓扑	电压等级	电流范围
U1	3 Phases IPM	600V	10~30A
U2	3 Phases IPM	600V	50A ~ 75A
U3	3 Phases IPM	600V	20A~30A
U4	3 Phases PIM	600V	5A ~ 15A

# 洗衣机

# 冰箱

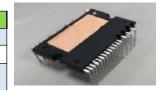








	变频洗衣机	
斯达产品	ID10FFT60U1S, GD08FFX60U4	
规格参数	规格参数 10A 600V IPM	
技术特点	Main stream packaging compliance, low thermal resistance	



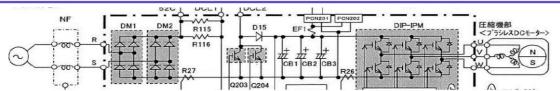
变频冰箱		
<b>斯达产品</b> GD08FFX60U4, DG5F06T3		4
规格参数	5A 600V	Ε
技术特点	Low profile, optional for PCB or heat-sink	















家用变频空调		
IPM	ID15FFT60U1S/ID30FFT60U1S/ID50FFT60 U2S	
IGBT	DG30F06T2/DG40F06T2	
FRD	DK60H06T3	









变频多联机		
IPM	ID50FFT60U2S	
PIM	GD50PIT120C5SN/GD75PIT120C6SN	
Rectifier	RD50FFS180K1S/RD75FFS180K1S	
IGBT	DG40F06T2	



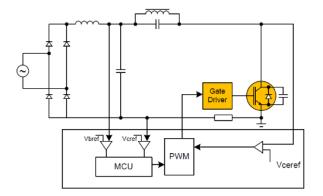




# 家用电磁炉(感应加热)







感应加热	
斯达产品	DG20R12T2
规格参数	20A 1200V 分离器件
技术特点	RC IGBT to reduce the conduction loss of the diode. High Breakdown Voltage, easily for replacement



**SEPR Converter Operation(Induction Cooker)** 

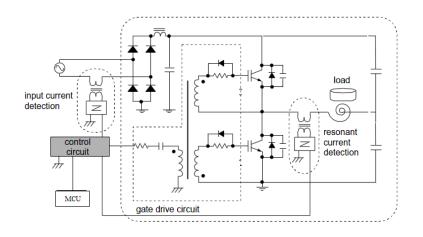


# 商用电磁炉(感应加热)









感应加热	
斯达产品	GD400HFU120C2 / GD100HFU120C1
规格参数	400A 1200V 100A 1200V
技术特点	High Ruggedness, Not easy to get thermal runaway



### We Offer

Quality

**Price** 

**Delivery** 

**Service** 





### Web Site



#### 关于我们

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#### 嘉兴斯达

塞·米斯达半导体配份有限公司成立于2005年4月,是一家专业从事功率半导体元器件尤其是IGBT研发、生产和销售服务的国家级高期技术企业,注册资金12亿元。总部位于浙江塞兴,占地106亩。在国内和欧洲均设有研发中心,是国内区研究的领军企业。

公司主要产品为助率半导体不器件,包括IOBT,MOSFET、IPM、FRD、SIC等等。公司已成功开发近600种 IOBT模块产品,电压等级温盖1007~33007、电流等级设 器、逆变焊机、UPS、光纺灰力发电、SVG、自色家电缆

公司在全球病者500多位员工(其中码环人员100多名 银棋員创新查说、创新激情和创新能力的国际型人才队伍 土,在IGBT 芯片和键块领域有着5-20年的研发和生产组 产品可靠性主验室和工况模拟主验室等等,可实现IGBT植 此外、公司也十分重视技术人员的培养,与浙江大学、中 盟。



### P1/P2 IGBT modules for solar and wind power applications

#### Typical applications

- High power solar inverter:
- Wind power convrerters
   Medium voltage high power inverters

#### Features

Industry standard packages

Products search

- 175°C junction temperature
   Soft switch waveform, suitable
- Soft switch waveform, suitable for high power paralleling



## 嘉兴斯达半导体

### 品质成就梦想 创新引领未来



Thank you

